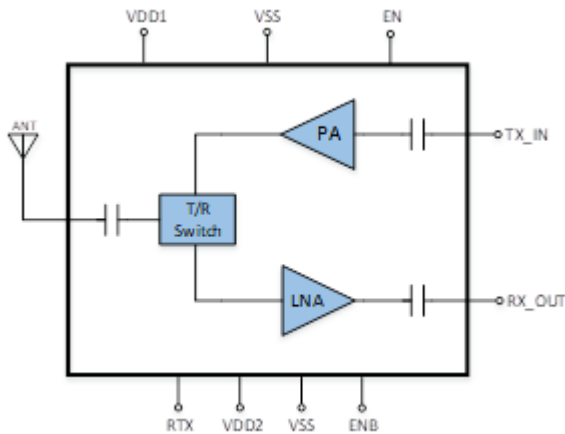


Product Overview

The ASF8001 is a GaAs PHEMT MMIC RF front end chip which operates from 33 to 36 GHz. The ASF8001 combines a low noise amplifier, power amplifier and one single-pole-double-throw (SPDT) switch; each can be switched on/off with a digital voltage of 0/2.5 V. The receive path offer 22.5 dB small signal gain and 4.2 dB noise figure. The measured output IP3 and output P1dB of receiver are 20.5 dBm and 11.2 dBm, respectively. The transmit path provides 16.5 dB of power gain, +25 dBm of saturated output power and 25% power added efficiency. The ASF8001 has a power handling capacity of +0.5 W continuous wave (CW) into the antenna port, eliminating the need for a limiter. All data is measured with the chip in a 50 Ohm test fixture connected via two 0.025 mm (1mil) diameter bond wires of minimal length 0.51 mm (20mil).

Functional Block Diagram



Key Features

1. Fully integrated, high performance front-end MMIC
2. Integrated DC blocking at RF input/output
3. Enable/Disable mode with digital signal
4. Bandwidth: 33 GHz to 36 GHz
5. RX Gain: 22.5 dB
6. RX Noise Figure: 4.2 dB
7. RX OTOI: 20.5 dBm
8. TX Power Gain: 16.5 dB
9. TX Saturated Output Power: 25.5 dBm
10. TX PAE: 25%
11. 50 Ohm Matched Input/output
12. Die Size: 2.75 x 2.55 x 0.1 mm

Applications

1. Communications
2. Phased Array Antenna

Main Electrical Specifications

Parameter	Min.	Typ.	Max.	Units
Frequency Range	33	-	36	GHz
TX Power Gain	17	19	19.5	dB
TX Psat	23.5	25	25.5	dBm
RX Gain	22	23	25	dB
RX Noise Figure	4	4.1	4.2	dB

Electrical Specifications, RX

Parameter	Min.	Typ.	Max.	Units
Frequency Range	33	-	36	GHz
Small Signal Gain	22	23	25	dB
Noise Figure	4	4.1	4.2	dB
Input Return Loss	15	-	-	dB
Output Return Loss	13	-	-	dB
Output Power for 1 dB Compression (P1dB)	-	11.2	-	dBm
Saturated Output Power	-	14.5	-	dBm
Output Third Order Intercept (IP3)	20.5	20.5	21	dBm
Supply Current (with RF)	-	55	-	mA

Test conditions unless otherwise noted: TA=+25 °C, VDD=3.5 V, VSS=-2.5 V, EN=2.5 V, ID=55 mA

Electrical Specifications, TX

Parameter	Min.	Typ.	Max.	Units
Frequency Range	33	-	36	GHz
Small Signal Gain	17	-	19.25	dB
Large Signal Gain	15.5	-	18	dB
Input Return Loss	12	-	-	dB
Saturated Output Power	-	25.5	-	dBm
Power Added Efficiency (@8dBm Pin)	22	25	27	%
Supply Current	-	30	-	mA

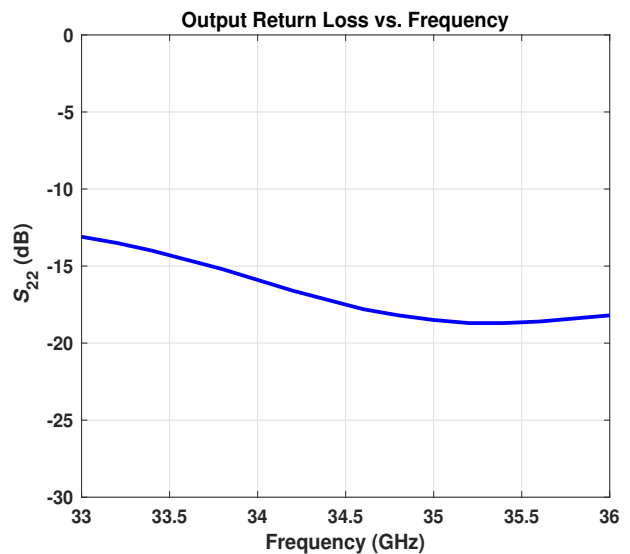
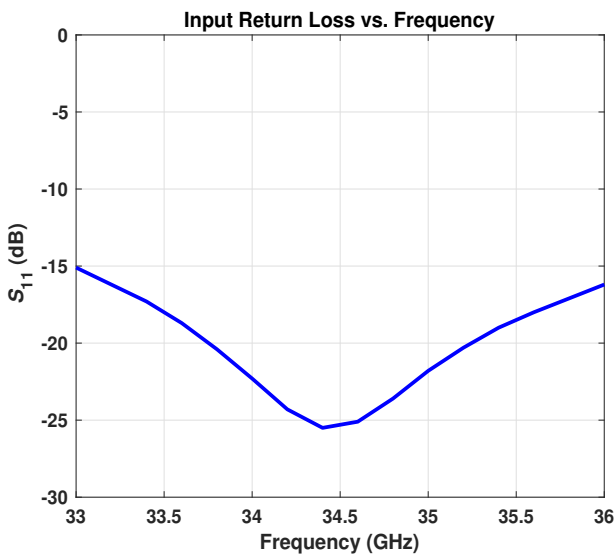
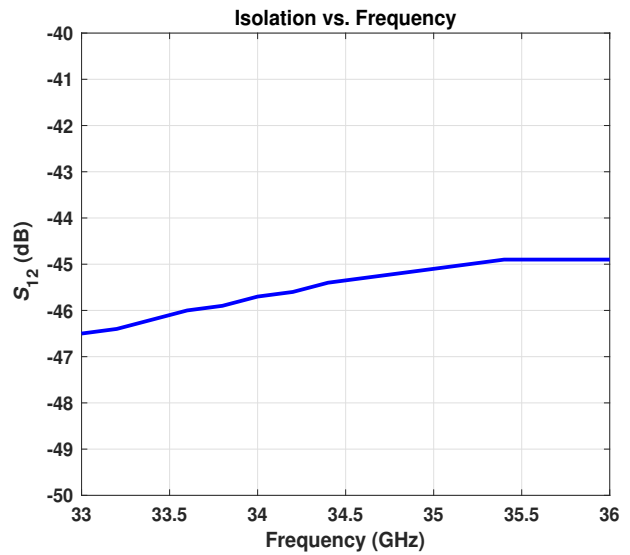
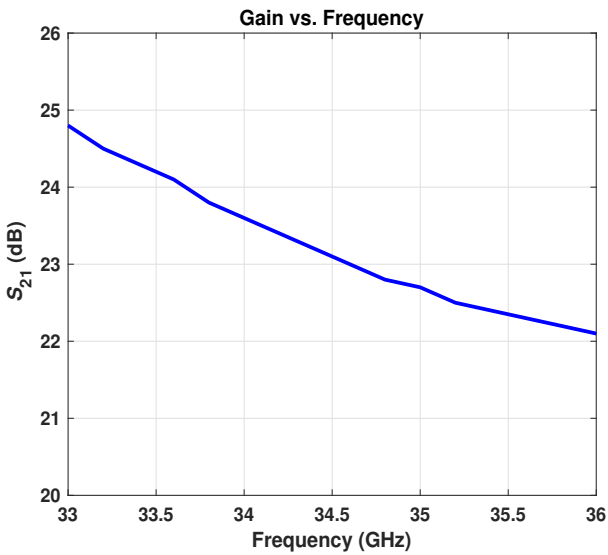
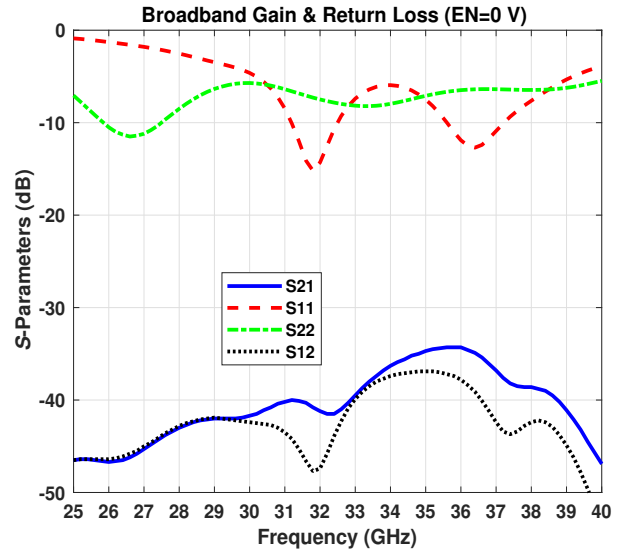
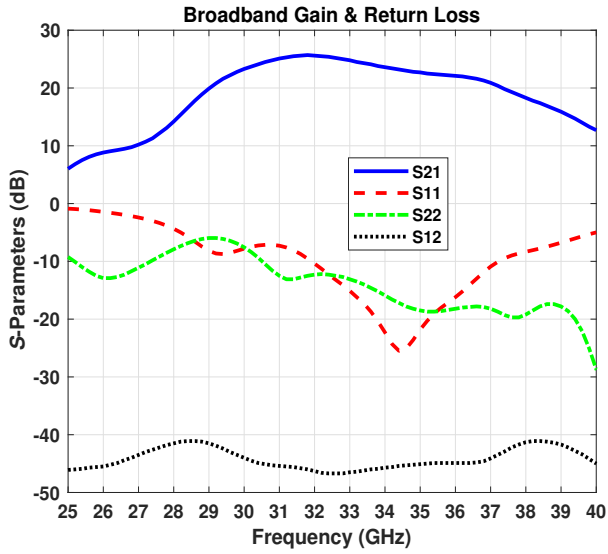
Test conditions unless otherwise noted: TA=+25 °C, VDD=3.5 V, VSS=-2.5 V, EN=2.5 V, ID=30 mA

Typical Bias Condition

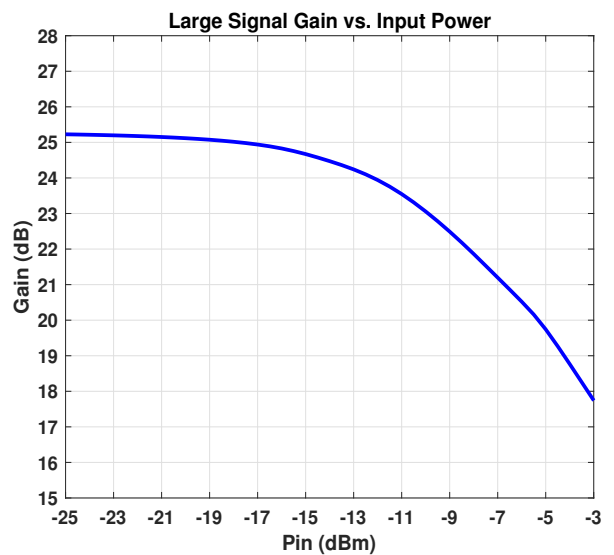
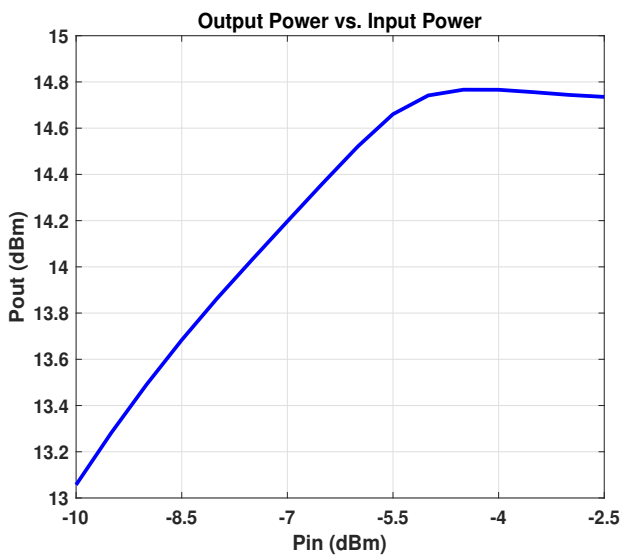
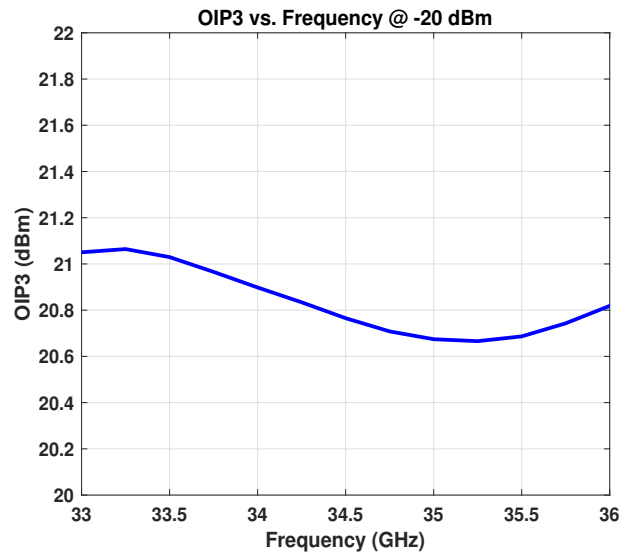
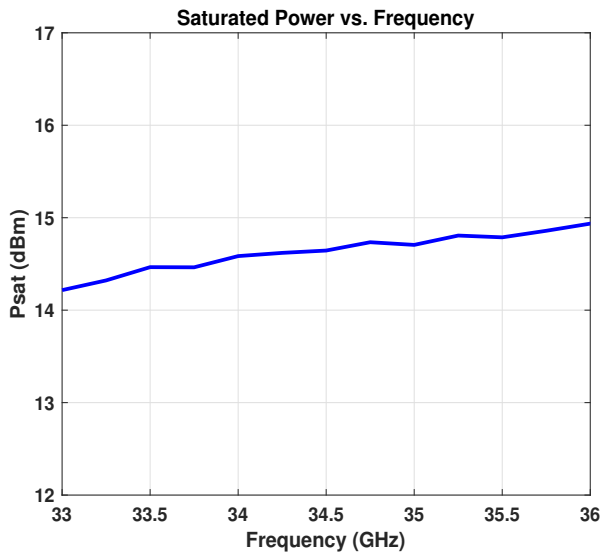
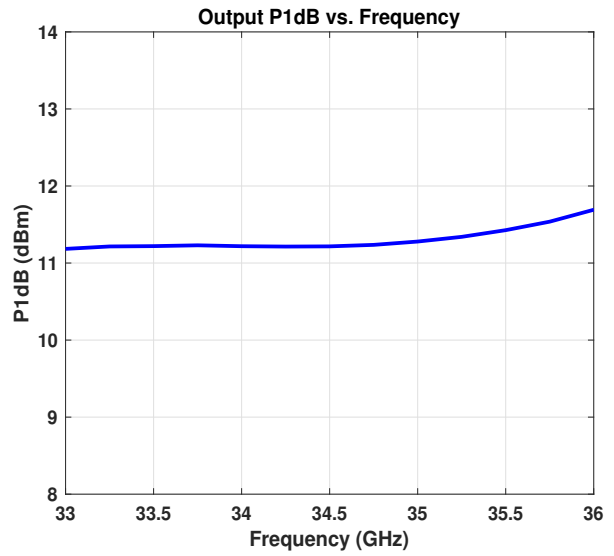
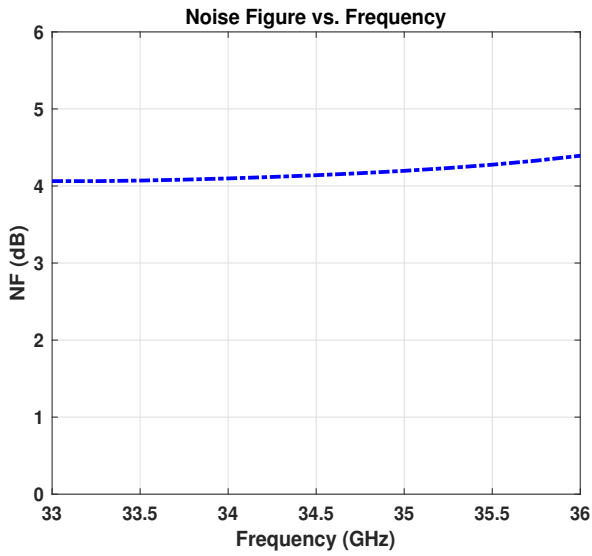
	TX-VDD	RX-VDD	VSS	TX-EN	RX-EN	RX/TX-EN	IDq
TX Mode	3.5 V	2.5 V	-2.5 V	2.5 V	0 V	2.5 V	30 mA
RX Mode	3.5 V	2.5 V	-2.5 V	0 V	2.5 V	0 V	55 mA

- NOTE1: Currents are measured at 25 °C
- NOTE2: The typical operation of amplifier is for supply voltages VSS = -2.5 V, VDD = 2.5 V.

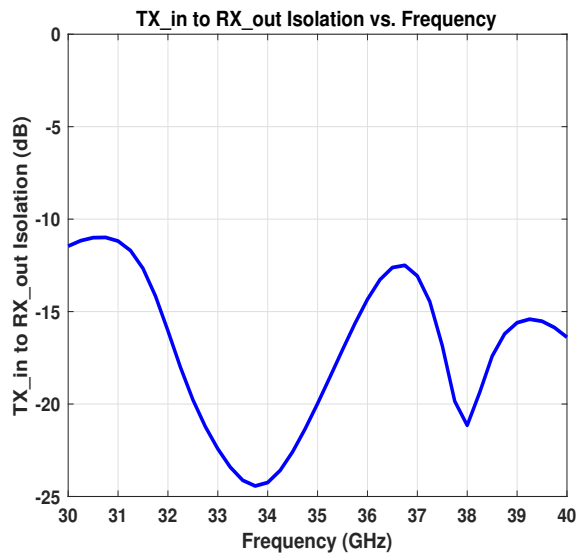
RX Performance Plots



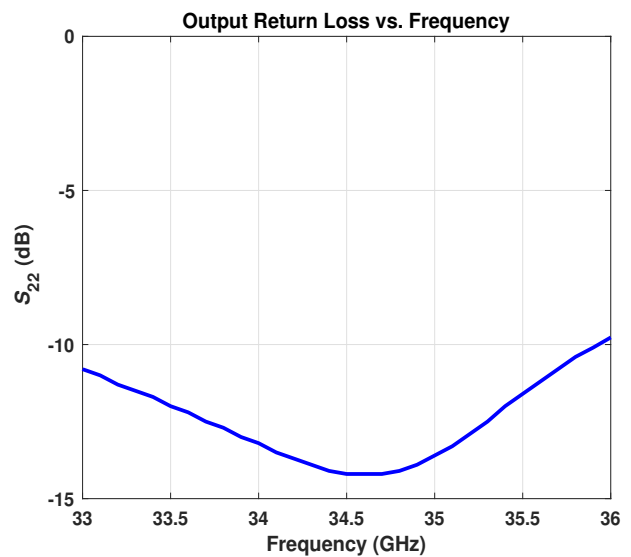
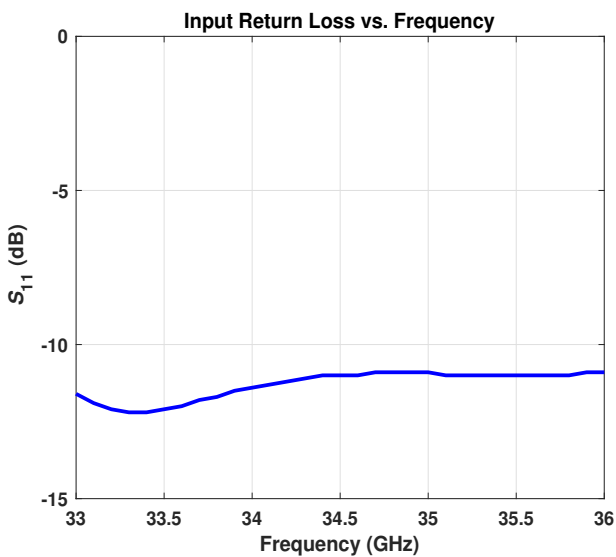
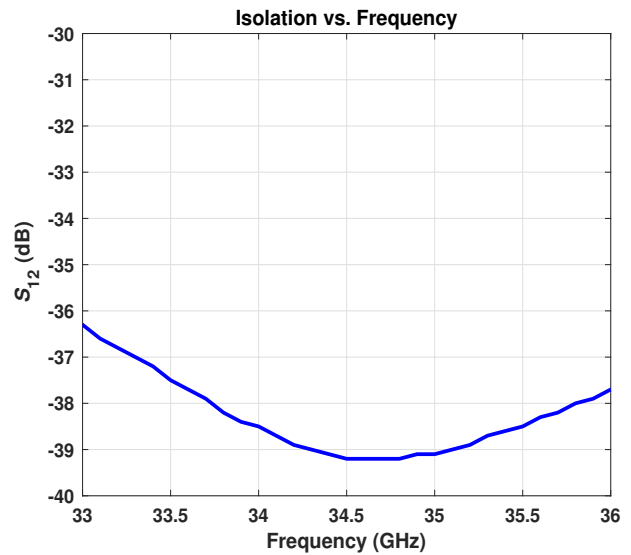
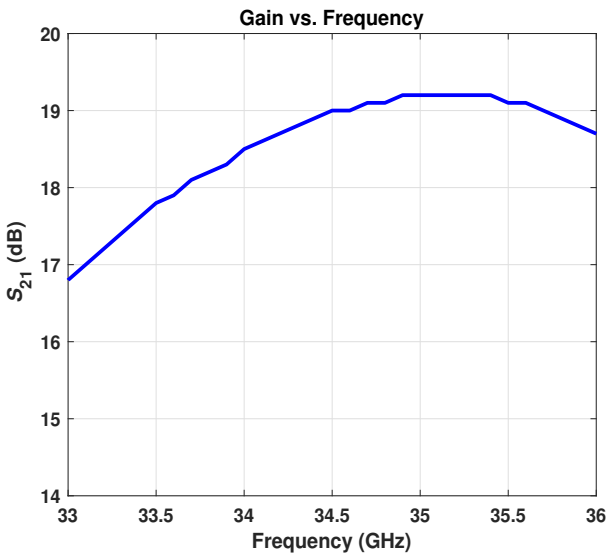
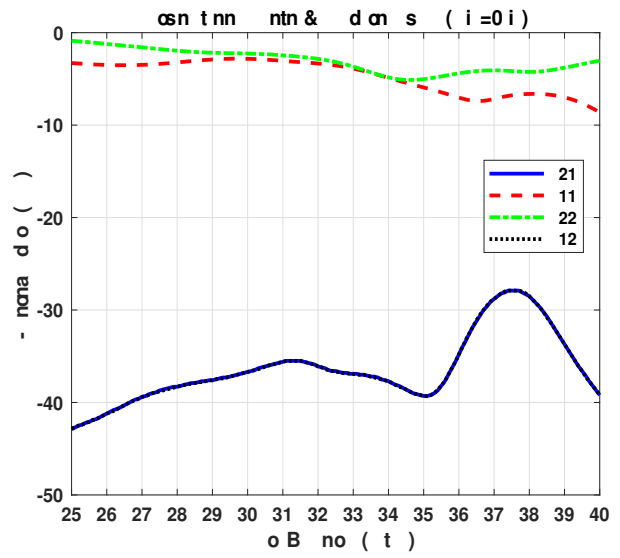
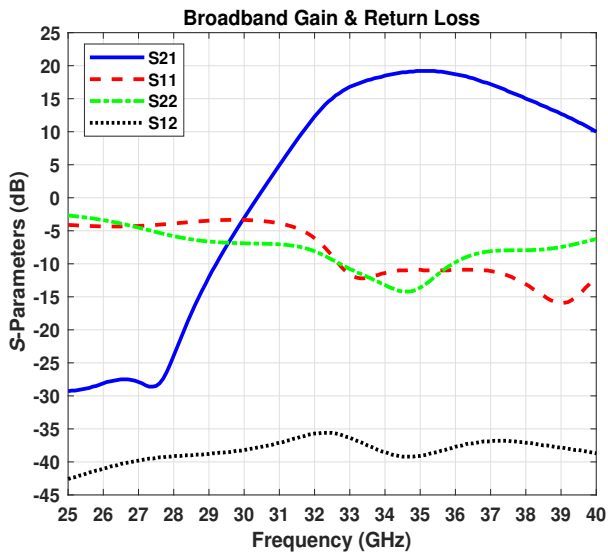
RX Performance Plots



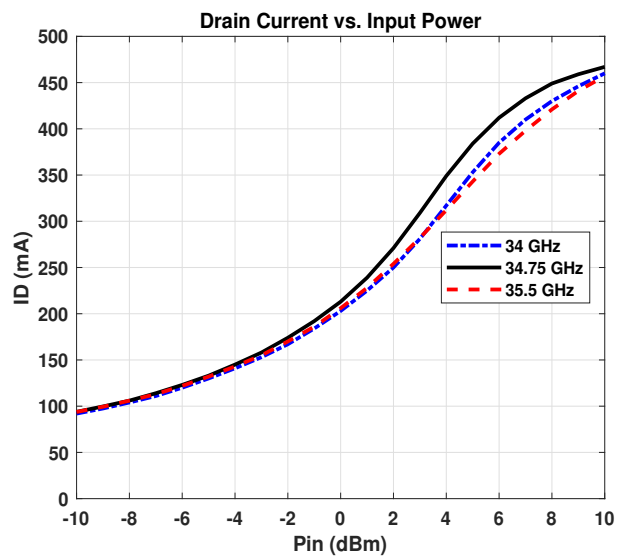
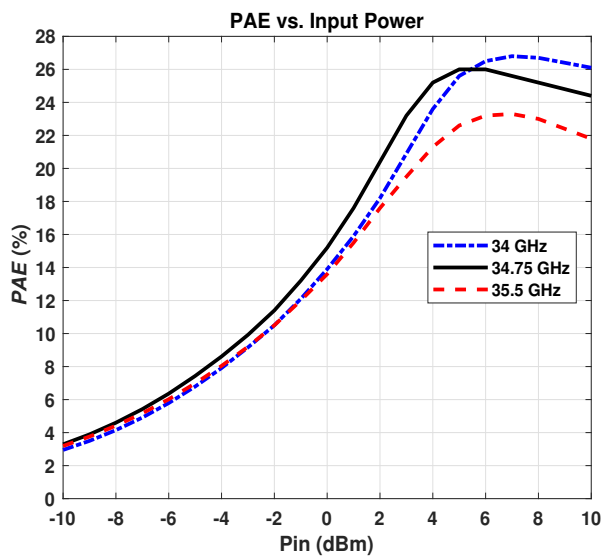
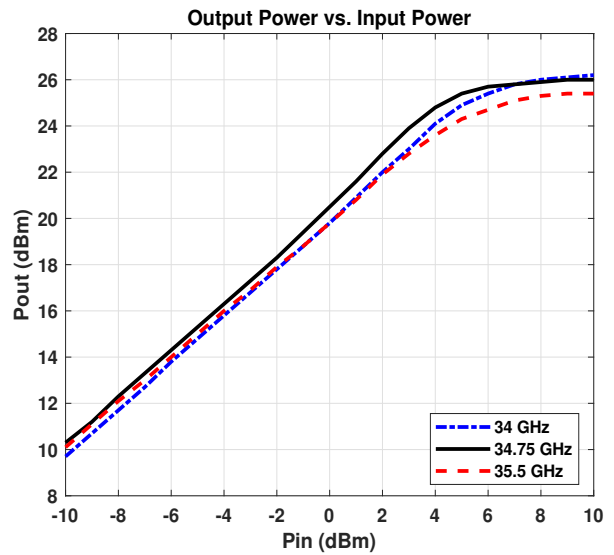
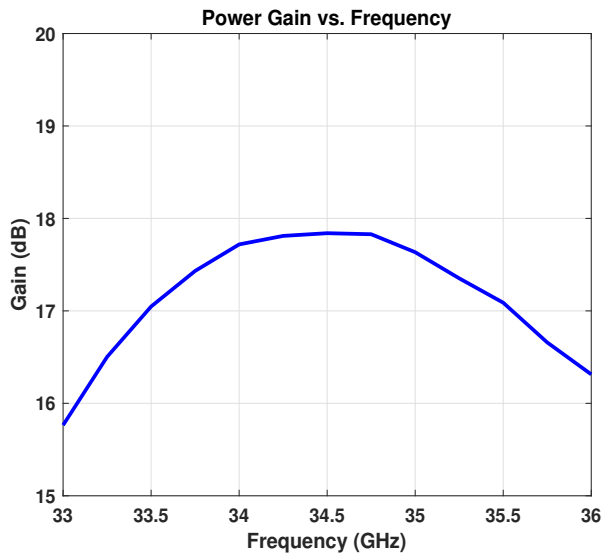
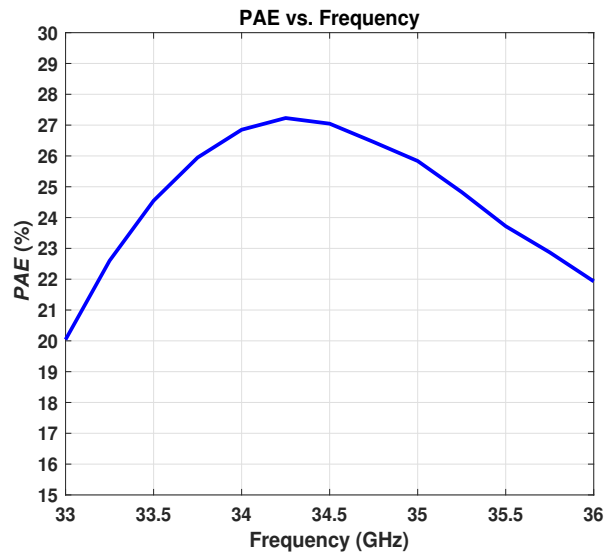
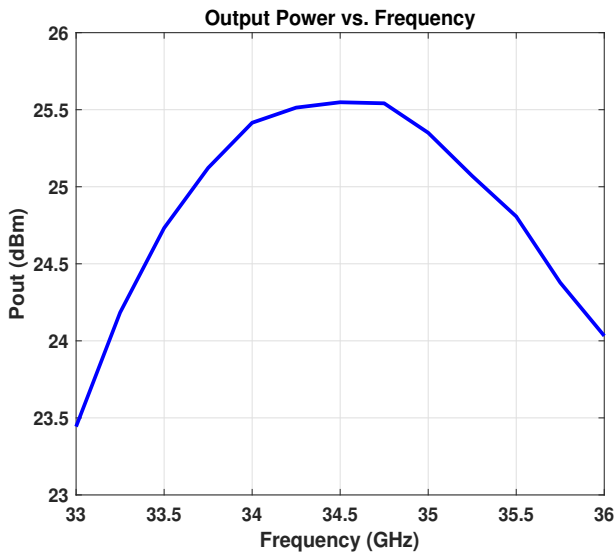
RX Performance Plots



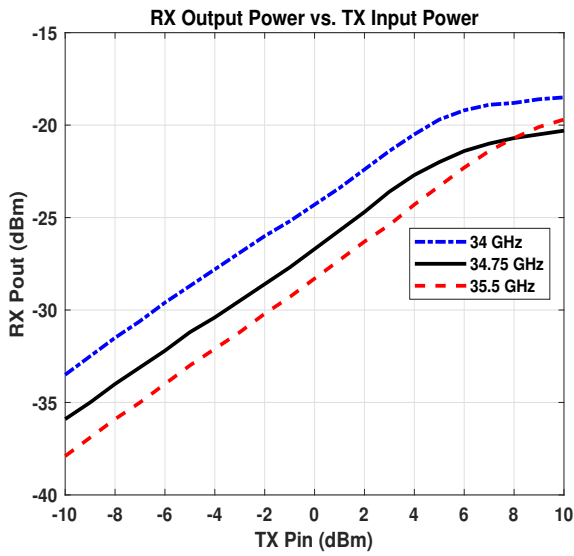
TX Performance Plots – Small Signal



TX Performance Plots – Large Signal



TX Performance Plots – Large Signal



Absolute Maximum Rating

Drain Bias Voltage	+3.5 Vdc
Gate Bias Voltage (VSS)	-3.5 Vdc
RF Input Power (CW, VDD=+2.5 Vdc)	26.5 dBm
TX RF Input Power (Pulsed, VDD=+2.5 Vdc)	29.5 dBm
Channel Temperature	175 °C
Continuous Power Dissipation (T=85°C)	0.55 W
Thermal Resistance (channel to ground pad)	55 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C



ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

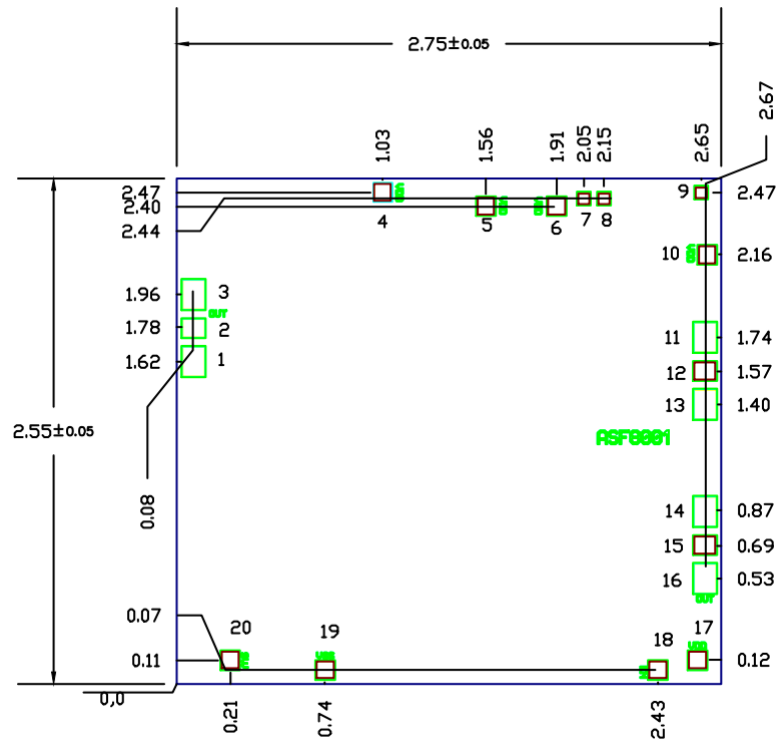
Bias-up Procedure

1. Ground the Device
2. Set VSS to -2.5V
3. Set TX-VDD to 3.5 V
4. Set RX-VDD to 2.5 V
5. Set RXTX-EN to 2.5V(TX) or to 0V(RX)
6. Set RX-EN to 2.5 V & TX-EN to 0 V(RX Mode)
7. Set RX-EN to 0 V & TX-EN to 2.5 V(TX Mode)
8. Apply RF Input Signal

Bias-down Procedure

1. Remove RF Input Signal
2. Set RX-EN & TX-EN & RXTX-EN to 0 V
3. Set TX-VDD & RX-VDD to 0 V
4. Set VSS to 0 V

Mechanical Information



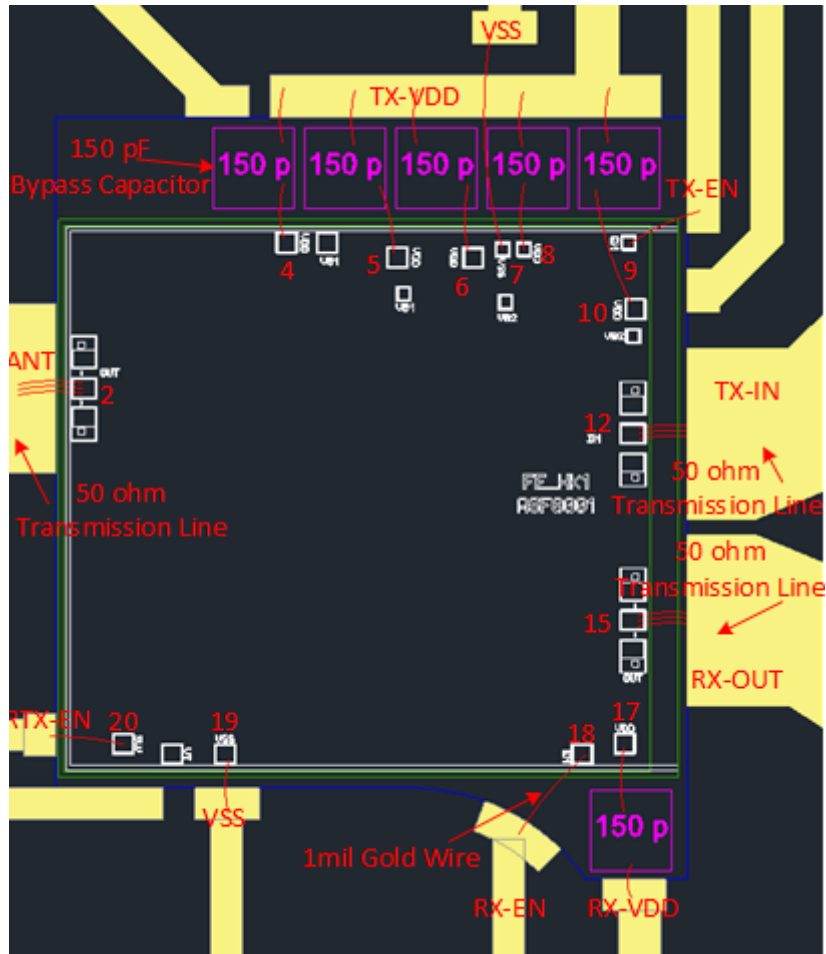
NOTES:

1. ALL DIMENSIONS IN MILLIMETERS
2. DIE THICKNESS IS $100 \mu\text{m}$
3. TYPICAL BOND PAD IS 0.01 mm^2
4. BACKSIDE METALLIZATION: GOLD
5. BACKSIDE METAL IS GROUND
6. BOND PAD METALIZATION: GOLD
7. NO CONNECTION REQUIRED FOR UNLABELED BOND PADS
8. OVERALL DIE SIZE $\pm 50 \mu\text{m}$

Bond Pad Description

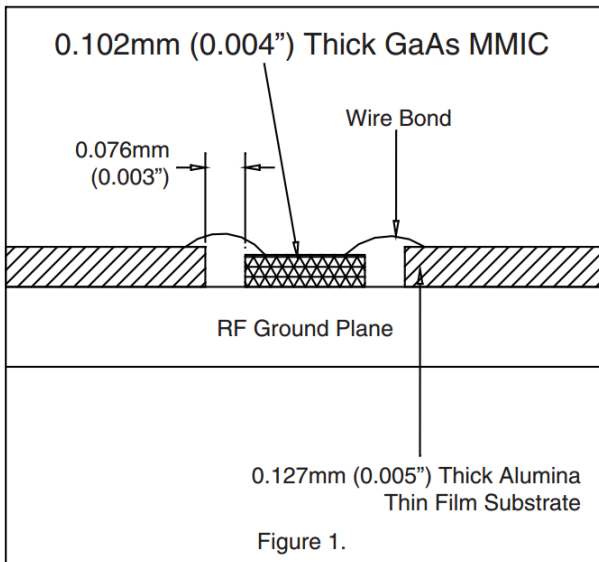
12	TX-IN	This pad is AC coupled and matched to 50 Ohms.
2	ANT	This pad is AC coupled and matched to 50 Ohms.
15	RX-OUT	This pad is AC coupled and matched to 50 Ohms.
1,3, 11,13,14,16 Die bottom	GND	These pads & die bottom are RF/DC ground. The die bottom must be connected to the RF/DC ground. Other pads connections are not required.
4,5,6,8,10	TX-VDD	Positive Supply Voltage for the PA. External bypass capacitors of 150 pF are required.
17	RX-VDD	Positive Supply Voltage for the LNA. External bypass capacitors of 150 pF are required.
7,19	VSS	Negative Supply Voltage for the PA & LNA.
18	RX-EN	This pad is for enabling/disabling of RX amplifier. (Active High) A digital signal 0/2.5 V with minimum current of 2 mA. This pad is pulled down internally.
9	TX-EN	This pad is for enabling/disabling of TX amplifier. (Active High) A digital signal 0/2.5 V with minimum current of 2 mA. This pad is pulled down internally.
20	RX/TX-EN	This pad is for RX/TX mode selection. Floating pad is not allowed.

Assembly Diagram



Mounting and Bonding Techniques for Millimeter wave GaAs MMICs

The die should be attached directly to the ground plane eutectically or with conductive epoxy. 50 Ohm Microstrip transmission lines on 0.127mm (5 mil) thick alumina thin film substrates are recommended for bringing RF to and from the chip (Figure 1). If 0.254mm (10 mil) thick alumina thin film substrates must be used, the die should be raised 0.150mm (6 mils) so that the surface of the die is coplanar with the surface of the substrate. One way to accomplish this is to attach the 0.102mm (4 mil) thick die to a 0.150mm (6 mil) thick molybdenum heat spreader (moly-tab) which is then attached to the ground plane (Figure 2). Microstrip substrates should be brought as close to the die as possible in order to minimize bond wire length. Typical die-to-substrate spacing is 0.076mm (3 mils)



Handling Precautions

Follow these precautions to avoid permanent damage.

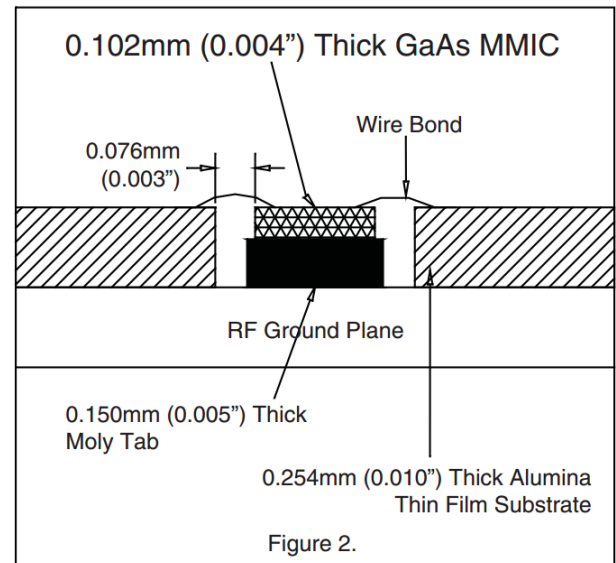
Storage: All bare dies are placed in either Waffle or Gel based ESD protective containers, and then sealed in an ESD protective bag for shipment. Once the sealed ESD protective bag has been opened, all die should be stored in a dry nitrogen environment.

Cleanliness: Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems. Static Sensitivity: Follow ESD precautions to protect against $>\pm 250V$ ESD strikes.

Transients: Suppress instrument and bias supply transients while bias is applied. Use shielded signal and bias cables to minimize inductive pick-up.

General Handling: Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers.

The surface of the chip has fragile air bridges and should not be touched with vacuum collet, tweezers, or fingers.



Mounting

The chip is back-metallized and can be die mounted with AuSn eutectic preforms or with electrically conductive epoxy. The mounting surface should be clean and flat.

Eutectic Die Attach: A 80/20 gold tin preform is recommended with a work surface temperature of 255 °C and a tool temperature of 265 °C. When hot 90/10 nitrogen/hydrogen gas is applied, tool tip temperature should be 290 °C. DO NOT expose the chip to a temperature greater than 320 °C for more than 20 seconds. No more than 3 seconds of scrubbing should be required for attachment.

Epoxy Die Attach: Apply a minimum amount of epoxy to the mounting surface so that a thin epoxy fillet is observed around the perimeter of the chip once it is placed into position. Cure epoxy per the manufacturer's schedule.

Wire Bonding

Ball or wedge bond with 0.025 mm (1 mil) diameter pure gold wire is recommended. Thermosonic wirebonding with a nominal stage temperature of 150 °C and a ball bonding force of 40 to 50 grams or wedge bonding force of 18 to 22 grams is recommended. Use the minimum level of ultrasonic energy to achieve reliable wirebonds. Wirebonds should be started on the chip and terminated on the package or substrate. All bonds should be as short as possible <0.5 mm (20 mils).

Contact Information

For the latest specifications, additional product information:

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Email: info@abba-semi.com